MOS FIELD EFFECT TRANSISTOR

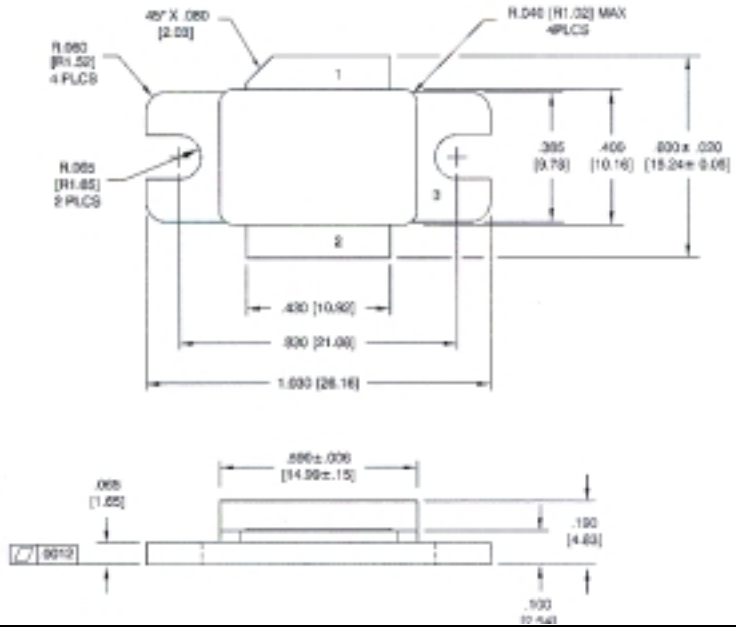
DESCRIPTION:

The **ASI PTF10019** is Designed for Cellular, GSM, and D-AMPS applicarions from 860 tp 960 MHz.

FEATURES:

- 70 W, 860-960 MHz
- Internally matched
- ***Omnigold***™ Metalization System
- Silicon Nitride Passivated

PACKAGE STYLE



1 = DRAIN 2 = GATE 3 = SOURCE

MAXIMUM RATINGS

V_{DSS}	65 V
V_{GS}	±20 V
P_{DISS}	215 W @ T_C = 25 °C
T_J	-40 °C to +200 °C
T_{STG}	-40 °C to +150 °C
θ_{JC}	0.8 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	V_{GS} = 0 v	I_D = 25 mA		65			V
I_{DSS}	V_{DS} = 26 V					1.0	mA
$V_{GS(th)}$	V_{DS} = 10 V	I_D = 75 mA		3.0		5.0	V
G_{fs}	V_{DS} = 10 V	I_D = 3.0 A			3.0		Siemens
P_G	V_{DD} = 28 V	P_{OUT} = 70 W	I_{DQ} = 600 mA	13.0	14.5		dB
η_C	f = 960 MHz			45	50		%
P-1dB				70	75		W
Ψ						10:1	---